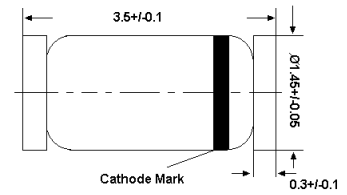


RLS245

Silicon Epitaxial Planar Diode

High Voltage Switching Diode

LL-34



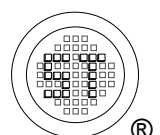
Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V_R	220	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Maximum Forward Current	I_{FM}	625	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25\text{ }^{\circ}\text{C}$	I_{FSM}	1000	mA
Junction Temperature	T_j	175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	1.5	V
Leakage Current at $V_R = 220\text{ V}$	I_R	-	10	μA
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	V_{BR}	250	-	V
Capacitance at $V_F = V_R = 0$, $f = 1\text{ MHz}$	C_{tot}	-	3	pF
Reverse Recovery Time from $I_F = I_R = 20\text{ mA}$	t_{rr}	-	75	ns



Dated : 15/06/2009